



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20251014001.2

**Qualification of CDAT as an additional Assembly/Test site for the Select Devices
Change Notification / Sample Request**

Date: October 14, 2025

To: Mouser PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within **60** days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within **60 days** of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the change management team.

For sample requests or sample related questions, contact your local Field Sales Representative.

Sincerely,

Change Management Team
SC Business Services

20251014001.2

Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
TLV70030QDCKRQ1	TLV70030QDCKRQ1
TLV70030QDCKRQ1	595-TLV70030QDCKRQ1
SN74LV1T34QDCKRQ1	NULL
INA186A2QDCKRQ1	NULL
TS5A3166QDCKRQ1	NULL
INA186A3QDCKRQ1	NULL

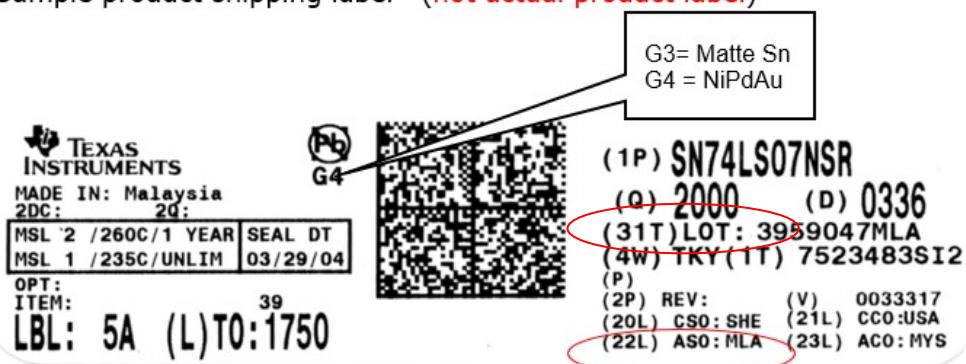
Technical details of this Product Change follow on the next page(s).

PCN Number:	PCN# 20251014001.2			PCN Date:	October 14, 2025																														
Title:	Qualification of CDAT as an additional Assembly/Test site for select devices																																		
Customer Contact:	Change Management Team		Dept:	Quality Services																															
Proposed 1st Ship Date:	April 12, 2026		Sample requests accepted until:	December 13, 2025*																															
*Sample requests received after December 13, 2025 will not be supported.																																			
Change Type:	<input checked="" type="checkbox"/> Assembly Site <input type="checkbox"/> Design <input type="checkbox"/> Wafer Bump Material <input checked="" type="checkbox"/> Assembly Process <input type="checkbox"/> Data Sheet <input type="checkbox"/> Wafer Bump Process <input checked="" type="checkbox"/> Assembly Materials <input type="checkbox"/> Part number change <input type="checkbox"/> Wafer Fab Site <input type="checkbox"/> Mechanical Specification <input checked="" type="checkbox"/> Test Site <input type="checkbox"/> Wafer Fab Material <input checked="" type="checkbox"/> Packing/Shipping/Labeling <input type="checkbox"/> Test Process <input type="checkbox"/> Wafer Fab Process																																		
PCN Details																																			
Description of Change:																																			
<p>Texas Instruments Incorporated is announcing the qualification of CDAT as an additional Assembly/Test site for the devices listed below. Construction differences are as follows:</p> <table border="1"> <thead> <tr> <th></th> <th>HFTF</th> <th>HNA</th> <th>TFME</th> <th>CDAT</th> </tr> </thead> <tbody> <tr> <td>Mount Compound</td> <td>4207123</td> <td>SID#A-09</td> <td>SID#A-09 SID# A-03</td> <td>4207123 4226215</td> </tr> <tr> <td>Bond wire diam/type</td> <td>0.8mil Cu</td> <td>1.0mil Au</td> <td>1.0mil Au</td> <td>0.8mil Cu</td> </tr> <tr> <td>Mold Compound</td> <td>SID#R-27</td> <td>SID#450179</td> <td>SID# R-07</td> <td>4222198</td> </tr> <tr> <td>Lead finish</td> <td>NiPdAu</td> <td>NiPdAu</td> <td>NiPdAu</td> <td>Matte Sn</td> </tr> <tr> <td>Wafer thickness</td> <td>6.0mil</td> <td>7.5mil</td> <td>7.5mil</td> <td>6.0mil</td> </tr> </tbody> </table>							HFTF	HNA	TFME	CDAT	Mount Compound	4207123	SID#A-09	SID#A-09 SID# A-03	4207123 4226215	Bond wire diam/type	0.8mil Cu	1.0mil Au	1.0mil Au	0.8mil Cu	Mold Compound	SID#R-27	SID#450179	SID# R-07	4222198	Lead finish	NiPdAu	NiPdAu	NiPdAu	Matte Sn	Wafer thickness	6.0mil	7.5mil	7.5mil	6.0mil
	HFTF	HNA	TFME	CDAT																															
Mount Compound	4207123	SID#A-09	SID#A-09 SID# A-03	4207123 4226215																															
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Lead finish	NiPdAu	NiPdAu	NiPdAu	Matte Sn																															
Wafer thickness	6.0mil	7.5mil	7.5mil	6.0mil																															
<p>Upon expiry of this PCN, TI will combine lead finish solutions in a single standard part number. For example, a customer order for 7500 units of a specific TI part number with 2500 units SPQ (Standard Pack Quantity per reel) may be fulfilled in the following ways:</p> <ul style="list-style-type: none"> • 3 reels of NiPdAu finish • 3 reels of Matte Sn finish • 2 reels of Matte Sn and 1 reel of NiPdAu finish • 2 reels of NiPdAu and 1 reel of Matte Sn finish 																																			
<p>Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ</p>																																			
<p>Qual details are provided in the Qual Data Section.</p>																																			
Reason for Change:																																			
Supply continuity																																			
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																																			
None																																			
Impact on Environmental Ratings																																			
<p>Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.</p>																																			
RoHS		REACH	Green Status	IEC 62474																															
<input checked="" type="checkbox"/> No Change		<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change																															

Changes to product identification resulting from this PCN:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
HFTF	HFT	CHN	Hefei
HNA	HNT	THA	Ayutthaya
TFME	NFM	CHN	Economic Development Zone
CDAT	CDA	CHN	Chengdu

Sample product shipping label (not actual product label)



Product Affected:

INA186A1QDCKRQ1*	INA186A3QDCKRQ1*	TLV70030QDCKRQ1
INA186A2QDCKRQ1*	SN74LV1T34QDCKRQ1	TS5A3166QDCKRQ1

* G4 part numbers are available and will remain on NiPdAu flows. This PCN does not apply to existing G4 materials. Please visit TI's [labeling and symbolization](#) page for more information on material designators

Automotive Qualification Summary
(As per AEC-Q100 Rev. J and JEDEC Guidelines)
 Approve Date 06-December-2024

Product Attributes

Attributes	Qual Device: INA210BODCKRTL	QBS Process Reference: INA215AQDCKRQ1	QBS Package Reference: TPS3840PH30DBVRO1	QBS Package Reference: LM74703ODDFRQ1	QBS Package Reference: TXS0101ODCKRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Signal Chain	Signal Chain	Power Management	Power Management	Logic
Wafer Fab Supplier	AIZU	AIZU	RFAB	RFAB	RFAB
Assembly Site	CDAT	TFME	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT	SOT	SOT
Package Designator	DCK	DCK	DBV	DDF	DCK
Pin Count	6	6	5	8	6

QBS: Qual By Similarity, also known as Generic Data

Qual Device [INA210BQDCKRTL](#) is qualified at MSL1 260C

Note 1: Qual device and affected devices in PCN have justification to use Package QBS references for HAST, AC/UHAST and TC-BP based on AEC-100J A1.3 assembly site and package attributes were qualified.

Note 2: Qual device and affected devices in PCN have justification to use Process QBS references for HTOL and ELFR based on AEC-100J A1.2 silicon wafer fab and process attributes were qualified. Group B tests purpose is for silicon defects, they do not get influenced by assembly site or BOM differences.

Note 3: Qual device and affected devices in PCN have justification to use SD QBS based on AEC-100J A1.3 leadframe attributes are qualified.

Note 4: One lot is allowed per AEC-Q100J A1.5.1 Multiple Sites - When the specific product or process attribute to be qualified or requalified will affect more than one wafer fab site or assembly site, a minimum of one lot of testing per affected site is required.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: INA210BQDKR01	QBS Process Reference: INA215AQDKR01	QBS Package Reference: TPS3840PH30DBVR01	QBS Package Reference: LM74703QDDFR01	QBS Package Reference: TXS0101QDKR01
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	1/Pass Note 4	-	3/Pass	3/Pass	3/Pass
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	1/77/0 Note 4	-	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0 Note 4	-	3/231/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	Note 1	-	1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	1/45/0 Note 4	-	3/135/0	1/45/0	3/135/0
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	Note 2	3/231/0	3/231/0	-	1/77/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	Note 2	-	-	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	Note 2	3/2400/0	-	-	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0 Note 4	1/30/0	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0 Note 4	1/30/0	3/90/0	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	Note 3	-	1/15/0	1/15/0	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	Note 3	-	1/15/0	1/15/0	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0 Note 4	-	3/30/0	3/30/0	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0 Note 4	-	-	-	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0 Note 4	-	-	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk<1.67 Room, hot, and cold	-	1/30/0 Note 4	-	-	-	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2405-062

Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 SOT at CDAT

Approve Date 06-December-2024

Attributes	Q006 Reference: <u>TPS3840PH30DBVRQ1</u>	Q006 Reference: <u>LM74703QDDFRQ1</u>	Q006 Reference: <u>TKS0101QDCKRQ1</u>
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Power Management	Power Management	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB
Assembly Site	CDAT	CDAT	CDAT
Package Group	SOT	SOT	SOT
Package Designator	DBV	DDF	DCK
Pin Count	5	8	6

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Q006 Reference: TPS3840PH30DBVRQ1	Q006 Reference: LM74703QDDFRQ1	Q006 Reference: TXS0101QDCKRQ1
Test Group A - Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/Pass	3/Pass	3/Pass
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	Note 1	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0	Note 1	3/3/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0	Note 1	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	Note 1	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	Note 1	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0	Note 1	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0	Note 1	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0	3/66/0	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0	3/3/0	3/3/0
TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	3/210/0	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0	3/3/0

TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0	3/9/0	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	1/45/0 Note 1	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0	1/1/0 Note 1	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0	1/44/0 Note 1	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	1/1/0 Note 1	3/3/0
Test Group C - Package Assembly Integrity Tests										
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	3/90/0

This report represents AEC-Q006 7.1 Family Data Usage using technology driver and lead products that are most representative of the technology family.

Note 1: LM74703QDDFRQ1 HAST and HTSL QBS'd to TPS3840PH30DBVRQ1 that has same Assembly site, package, bond pad metal, wire and mold attributes.

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E) : -40C to +150C

Grade 1 (or Q) : -40C to +125C

Grade 2 (or T) : -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2405-062

Automotive New Product Qualification Summary (As per AEC-Q100 Rev. J and JEDEC Guidelines)

Approve Date 02-July-2025

Product Attributes

Attributes		Qual Device: CAHC1G125QDCKRQ1		QBS Process Reference: SN74HCS74QPWRQ1		QBS Package Reference: TL331QDBVRQ1		QBS Package, Product Reference: CAHCT1G125QDBVRQ1		QBS Package Reference: TXS0101QDCKRQ1	
Automotive Grade Level		Grade 1		Grade 1		Grade 1		Grade 1		Grade 1	
Operating Temp Range (C)		-40 to 125		-40 to 125		-40 to 125		-40 to 125		-40 to 125	
Product Function		Signal Chain, Logic		Logic		Signal Chain		Logic		Logic	
Wafer Fab Supplier		RFAB		RFAB		RFAB		RFAB		RFAB	
Assembly Site		CDAT		MLA		CDAT		CDAT		CDAT	
Package Group		SOT		TSSOP		SOT		SOT		SOT	
Package Designator		DCK		PW		DBV		DBV		DCK	
Pin Count		5		14		5		5		6	

QBS: Qual By Similarity, also known as Generic Data

Qual Device CAHC1G125QDCKRQ1 is qualified at MSL1 260C

Per AEC-Q100J A1.3: The PCN devices are categorized as a qualification family and use generic data that has been qualified for the critical attributes in Die sizes, Package Type, Assembly Process and Site

Note 1: Qual Device and affected devices in PCN have justification to use Package and Process QBS references for Group A, Group B and Group C tests based on AEC-100J Appendix 1 A1.2 and A1.3. The fab, assembly site and package attributes were qualified.

Note 2: Other devices have passed HBM/CDM/LU with the final wafer/backgrind thickness. TI will not re-run HBM/CDM/LU for this change since backgrind removes bulk silicon and does not affect the active area of die.

HBM/CDM/LU purpose is to test the active area of die, die circuit design and/or wafer fab defects that would result damage to dielectrics, junctions, metal.

Note 3: ED cannot use Generic data per AEC-Q100J but there is representation of passing Electrical Distributions in QBS Package devices with the same assembly site and package attributes.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: CAHC1G125QDCKRQ1	QBS Process Reference: SN74HCS74QPWRQ1	QBS Package Reference: TL331QDBVRQ1	QBS Package, Product Reference: CAHCT1G125QDBVRQ1	QBS Package Reference: TXS0101QDCKRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	Note 1	-	3/Pass	3/Pass	3/Pass
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	1/77/0	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	Note 1	-	3/231/0	1/77/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	Note 1	-	3/231/0	1/77/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	Note 1	-	1/6/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	Note 1	-	-	-	3/135/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	Note 1	-	1/45/0	1/45/0	-
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	Note 1	3/231/0	-	-	3/231/0
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	150C	300 Hours	Note 1	-	1/77/0	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	Note 1	3/2400/0	-	-	-
Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0	3/90/0

SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	Note 1	1/15/0	1/15/0	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	Note 1	1/15/0	1/15/0	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	3/30/0	1/10/0	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements				
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements				
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements				
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements				
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements				
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Note 2	-	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	Note 2	-	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	Note 2	-	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	Note 3	-	1/30/0	1/30/0	3/90/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2502-024

Automotive Qualification Summary (As per AEC and JEDEC Guidelines)

Q006 SOT at CDAT

Approve Date 02-July-2025

Attributes		QBS Package Reference: TXS0101QDCKRQ1	
Automotive Grade Level		Grade 1	
Operating Temp Range (C)		-40 to 125	
Product Function		Logic	
Wafer Fab Supplier		RFAB	
Assembly Site		CDAT	
Package Group		SOT	
Package Designator		DCK	
Pin Count		6	

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	QBS Reference: TXS0101QDCKRQ1
Test Group A - Accelerated Environment Stress Tests								
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	3/Pass
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0
HAST	A2.1.3	-	3	3	Wire Bond Shear, post bHAST, 1X	Post stress	-	3/9/0
HAST	A2.1.4	-	3	3	Bond Pull over Stitch, post bHAST, 1X	Post stress	-	3/9/0
HAST	A2.1.5	-	3	3	Bond Pull over Ball, post bHAST, 1X	Post stress	-	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	70	Biased HAST	130C/85%RH	192 Hours	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0
HAST	A2.2.3	-	3	3	Wire Bond Shear, post bHAST, 2X	Post stress	-	3/9/0
HAST	A2.2.4	-	3	3	Bond Pull over Stitch, post bHAST, 2X	Post stress	-	3/9/0
HAST	A2.2.5	-	3	3	Bond Pull over Ball, post bHAST, 2X	Post stress	-	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0

TC	A4.1.3	-	3	3	Wire Bond Shear, post TC, 1X	Post stress	-	3/9/0
TC	A4.1.4	-	3	3	Bond Pull over Stitch, post TC, 1X	Post stress	-	3/9/0
TC	A4.1.5	-	3	3	Bond Pull over Ball, post TC, 1X	Post stress	-	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	70	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
TC	A4.2.3	-	3	3	Wire Bond Shear, post TC, 2X	Post stress	-	3/9/0
TC	A4.2.4	-	3	3	Bond Pull over Stitch, post TC, 2X	Post stress	-	3/9/0
TC	A4.2.5	-	3	3	Bond Pull over Ball, post TC, 2X	Post stress	-	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	44	High Temperature Storage Life	150C	2000 Hours	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0

Test Group C - Package Assembly Integrity Tests

WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0

This report represents AEC-Q006 7.1 Family Data Usage using technology driver and lead products that are most representative of the technology family.

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TI Qualification ID: R-CHG-2502-024

ZVEI IDs: SEM-PW-03, SEM-PA-05, SEM-PA-07, SEM-PA-08, SEM-PA-11, SEM-PA-18, SEM-TF-01

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Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

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